IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

Bao et al.

Serial No.:

10/671,303

Filed:

September 24, 2003

For:

SEMICONDUCTOR DEVICES HAVING

REGIONS OF INDUCED HIGH AND LOW

CONDUCTIVITY, AND METHODS OF

MAKING THE SAME

Group:

2812

Examiner:

Not Yet Assigned

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Name: Karen S. Flyr

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Durham, North Carolina February 17, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER § 197(a)

Sir:

This Information Disclosure Statement is being filed before a first Official Action has been mailed in this case.

Pursuant to 37 C.F.R. 1.56, 1.97 and 1.98, applicant's attorney wishes to bring to the attention of the Patent and Trademark Office the following items listed on the accompanying Forms PTO/SB/08A and PTO/SB/08B.

ITEMS

	Document No.	Publication	Patentee/Applicant
1.	U.S. Patent No. 5,192,580	<u>Date</u> 03/09/1993	Blanchet-Fincher
2.	U.S. Patent No. 5,288,528	02/22/1994	Blanchet-Fincher
3.	U.S. Patent No. 5,347,144	09/13/1994	Garnier et al.
4.	U.S. Patent No. 5,523,192	06/04/1996	Blanchet-Fincher
5.	U.S. Patent No. 5,563,019	10/08/1996	Blanchet-Fincher
6.	U.S. Patent No. 5,625,199	04/29/1997	Baumbach et al.
7.	U.S. Patent No. 5,766,819	06/16/1998	Blanchet-Fincher
8.	U.S. Patent No. 5,840,463	11/24/1998	Blanchet-Fincher
9.	U.S. Patent No. 5,981,970	11/09/1999	Dimitrakopoulos et al.
10.	U.S. Patent No. 6,051,318	04/18/2000	Kwon
11.	U.S. Patent No. 6,143,451	11/07/2000	Blanchet-Fincher
12.	U.S. Patent No. 6,146,792	11/14/2000	Blanchet-Fincher et al.
13.	U.S. Patent No. 6,174,651	01/16/2001	Thakur
14.	U.S. Patent No. 6,265,243	07/24/2001	Katz et al.
15.	U.S. Patent No. 6,352,811	03/05/2002	Patel et al.
16.	U.S. Patent No. 6,352,812	03/05/2002	Shimazu et al.
17.	U.S. Patent No. 6,403,397	06/11/2002	Katz
18.	U.S. Patent No. 6,551,717	04/22/2003	Katz et al.
19.	U.S. Publication No. 2002/0149315 A1	10/17/2002	Blanchet-Fincher
20.	U.S. Application No. 10/256,885	09/27/2002	Bao et al.
21.	U.S. Application No. 10/669,780	09/24/2003	Bao

22.	U.S. Application No. 60/505,533	09/24/2003	Meth
23.	U.S. Application No. 60/505,880	09/24/2003	Meth et al.
24.	U.S. Application No. 10/701,183	11/04/2003	Akkerman et al.
25.	U.S. Application No. 10/722,613	11/26/2003	Aizenberg et al.
26.	PCT Publication No. WO 01/87634 A2	11/22/2001	E.I. du Pont de Nemours and Company
27.	PCT Publication No. WO 02/08801 A1	01/31/2002	E.I. du Pont de Nemours and Company
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The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made nor shall it be construed as an admission that the information cited is considered to be material to patentability, nor shall it be construed that no other material information exists.

Respectfully submitted,

Jay M. Brown Reg. No. 30,033

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C. Brancis

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Su	bstitute for form 1449A/PTO			Complete if Known		
	bounded for form 1440701 10			Application Number	10/671,303	
01	NFORMATION DIS	SCLOS	JRE	Filing Date	09/24/2003	
	STATEMENT BY A	PPLICA	ant	First Named Inventor	Bao et al.	
	(Use as many sheets as	necessary)		Art Unit	2812	
				Examiner Name		
Sheet	1	of	5	Attorney Docket Number	100.2495	

			U.S. PATENT	DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number Number - Kind Code ² (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US- 5,192,580	03/09/1993	Blanchet-Fincher	
	2	US- 5,288,528	02/22/1994	Blanchet-Fincher	
	3	US- 5,347,144	09/13/1994	Gamier et al.	
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	14	US- 6,265,243	07/24/2001	Katz et al.	
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	16	US- 6,352,812	03/05/2002	Shimazu et al.	· · · · · · · · · · · · · · · · · · ·
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***************************************	19	US- 2002/0149315 A1	10/17/2002	Blanchet-Fincher	M
	20	US- 10/256,885	09/27/2002	Bao et al.	

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		Foreign Patent Document	Publication Date	Name of Patentee or	Pages, Columns, Lines,	Т
Examiner Initials*	1000	Country Code ³ - Number ⁴ - Kind Code ⁵ (<i>if known</i>)	MM-DD-YYYY	Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	
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				Co	mplete if Known
Su	bstitute for form 1449A/PTO			Application Number	10/671,303
	NFORMATION DISCL	∩ei	IDE	Filing Date	09/24/2003
				First Named Inventor	Bao et al.
5	STATEMENT BY APP	LIC	ANI	Art Unit	2812
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Sheet	2	of	5	Attorney Docket Number	100.2495

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	21	US- 10/669,780	09/24/2003	Bao	
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	23	US- 60/505,880	09/24/2003	Meth et al.	
	24	US- 10/701,183	11/04/2003	Akkerman et al.	
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	26	WO 01/87634 A2	11/22/2001	E.I. du Pont de Nemours and Company				
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				Application Number	10/671,303
INF	ORMATION DIS	CLOS	JRE	Filing Date	09/24/2003
STA	TEMENT BY A	PPLIC/	TMA	First Named Inventor	Bao et al.
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		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	29	AFZALI ET AL., High-Performance, Solution-Processed Organic Thin Film Transistors from a Novel Pentacene Precursor, J. Am. Chem. Soc., 2002, Page(s) 8812-8813, Volume 124	
NT 468-91 0 144-97 0 180-97 91 17 0 180-99	30	AFZALI ET AL., Synthesis and Application of Pentacene Precursor in OTFT, Publisher: IBM Research Division, Published in: Yorktown Heights, NY	
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	41	FORREST, Ultrathin Organic Films Grown by Organic Molecular Beam Deposition and Related Techniques, Chem. Rev., Page(s) 1793-1896, Volume 97, Publisher: American Chemical Society				
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PTO/SB/08b (08-03)

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				Application Number	10/671,303	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Filing Date	09/24/2003	
				First Named Inventor	Bao et al.	
				Art Unit	2812	
				Examiner Name		
Sheet	5	of	5	Attorney Docket Number	100.2495	

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No.	and/or country where published.	T ²			
	54	SEO ET AL., Interpretation of the Mass Change Behavior in the Binary Monolayer of Hydroquinone-tethered Alkylthiol and Aminoalkythiol, Bull. Korean Chem. Soc., 2002, Page(s) 1671-1673, Volume 23, Number 11				
	55	STABEL ET AL., Scanning Tunneling Microscopy of Alkylated Oligothiophenes at Interfaces with Graphite, Synthetic Metals, 1994, Page(s) 47-53, Volume 67				
	56	TANIMOTO ET AL., Binary Phase Chlorination of Aromatic Hydrocarbons with Solid Copper(II) Chloride: Reaction Mechanism, Bull. Chem. Soc. Japan, 1979, Page(s) 3586-3591, Volume 52, Number 12				
	57	XIA ET AL., Soft Lithography, Angew. Chem. Int. Ed., 1998, Page(s) 550-575, Volume 37				
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